

PATENT APPLICATION FEE DETERMINATION RECORD
Effective January 1, 2003

Application or Docket Number

10609075

CLAIMS AS FILED - PART I

	(Column 1)	(Column 2)
TOTAL CLAIMS	18	
FOR	NUMBER FILED	NUMBER EXTRA
TOTAL CHARGEABLE CLAIMS	18 minus 20=	*
INDEPENDENT CLAIMS	3 minus 3 =	*
MULTIPLE DEPENDENT CLAIM PRESENT <input type="checkbox"/>		

* If the difference in column 1 is less than zero, enter "0" in column 2

CLAIMS AS AMENDED - PART II

	(Column 1)	(Column 2)	(Column 3)
AMENDMENT A	CLAIMS REMAINING AFTER AMENDMENT	HIGHEST NUMBER PREVIOUSLY PAID FOR	PRESENT EXTRA
	Total	* 16 Minus ** 20 =	
	Independent	* 2 Minus *** 3 =	
	FIRST PRESENTATION OF MULTIPLE DEPENDENT CLAIM <input type="checkbox"/>		

	(Column 1)	(Column 2)	(Column 3)
AMENDMENT B	CLAIMS REMAINING AFTER AMENDMENT	HIGHEST NUMBER PREVIOUSLY PAID FOR	PRESENT EXTRA
	Total	* Minus ** =	
	Independent	* Minus *** =	
	FIRST PRESENTATION OF MULTIPLE DEPENDENT CLAIM <input type="checkbox"/>		

	(Column 1)	(Column 2)	(Column 3)
AMENDMENT C	CLAIMS REMAINING AFTER AMENDMENT	HIGHEST NUMBER PREVIOUSLY PAID FOR	PRESENT EXTRA
	Total	* Minus ** =	
	Independent	* Minus *** =	
	FIRST PRESENTATION OF MULTIPLE DEPENDENT CLAIM <input type="checkbox"/>		

* If the entry in column 1 is less than the entry in column 2, write "0" in column 3.

** If the "Highest Number Previously Paid For" IN THIS SPACE is less than 20, enter "20."

*** If the "Highest Number Previously Paid For" IN THIS SPACE is less than 3, enter "3."

The "Highest Number Previously Paid For" (Total or Independent) is the highest number found in the appropriate box in column 1.

SMALL ENTITY TYPE ☐

OR OTHER THAN SMALL ENTITY

RATE	FEE		RATE	FEE
BASIC FEE	375.00	OR	BASIC FEE	750.00
X\$ 9=		OR	X\$18=	
X42=		OR	X84=	
+140=		OR	+280=	
TOTAL		OR	TOTAL	750

SMALL ENTITY OR OTHER THAN SMALL ENTITY

RATE	ADDITIONAL FEE		RATE	ADDITIONAL FEE
X\$ 9=		OR	X\$18=	
X42=		OR	X84=	
+140=		OR	+280=	
TOTAL ADDIT. FEE		OR	TOTAL ADDIT. FEE	

RATE	ADDITIONAL FEE		RATE	ADDITIONAL FEE
X\$ 9=		OR	X\$18=	
X42=		OR	X84=	
+140=		OR	+280=	
TOTAL ADDIT. FEE		OR	TOTAL ADDIT. FEE	

RATE	ADDITIONAL FEE		RATE	ADDITIONAL FEE
X\$ 9=		OR	X\$18=	
X42=		OR	X84=	
+140=		OR	+280=	
TOTAL ADDIT. FEE		OR	TOTAL ADDIT. FEE	

SEP 27 2004

Docket: P910322

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Hsu et al.

Serial No.: 10/609,075

Filed: June 27, 2003

For: NON-VOLATILE MEMORY
CELL WITH DIELECTRIC
SPACERS ALONG SIDEWALLS
OF A COMPONENT STACK,
AND METHOD FOR FORMING
SAME

Examiner: Nadav, Ori

Group Art Unit: 2811

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

CERTIFICATE OF FACSIMILE TRANSMISSION
I hereby certify that this paper is being facsimile
transmitted to: Commissioner for Patents at fax number 703-308-
7722 on September 27, 2004.


Kenton R. Mullins, Reg. No. 36,331AMENDMENT

Dear Sir:

This is in response to the non-final Office Action mailed from the United States Patent and Trademark Office on May 28, 2004 in the above-referenced application. An appropriate extension of time is being filed concurrently herewith.

Amendments to the Detailed Description begin on page 2 of this paper.

Amendments to the Claims are reflected in the listing of claims which begins on page 3 of this paper.

10/07/2004 GLENIS 00000002 501/00 10/09075
Remarks begin on page 7 of this paper.

01 FC:1251 110.00 DA

Application No. 10/609,075
September 24, 2004
Page 2

Docket: P910322

Amendments to the Detailed Description

Please amend the paragraph bridging pages 7 and 8 to read as follows:

Referring to the drawings, FIGS. 2-9B will now be used to describe one embodiment of a method for forming localized trapped charge memory cell structures. FIG. 2 is a cross-sectional view of a semiconductor substrate 120 having an electron trapping structure comprising a first silicon dioxide (oxide) layer 122 formed on an upper surface, a silicon nitride (nitride) layer 124 formed over the first oxide layer 122, and a second oxide layer 126 formed over the nitride layer 124 ~~and a~~ A polycrystalline silicon (polysilicon) layer 128 is formed over the second oxide layer 126.

SEP 27 2004

Docket: P910322

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Hsu et al.

Serial No.: 10/609,075

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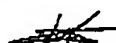
For: NON-VOLATILE MEMORY CELL
WITH DIELECTRIC SPACERS
ALONG SIDEWALLS OF A
COMPONENT STACK, AND
METHOD FOR FORMING SAME

Examiner: Nadav, Ori

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Kenton R. Mullins, Reg. No. 36,331

TRANSMITTAL

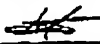
Sir:

Submitted herewith are

- ~ Amendment (9 pages including this Transmittal);
- ~ The Commissioner is hereby authorized to charge any needed fees to deposit account 50-1600.

Respectfully submitted,

Date: September 27, 2004


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